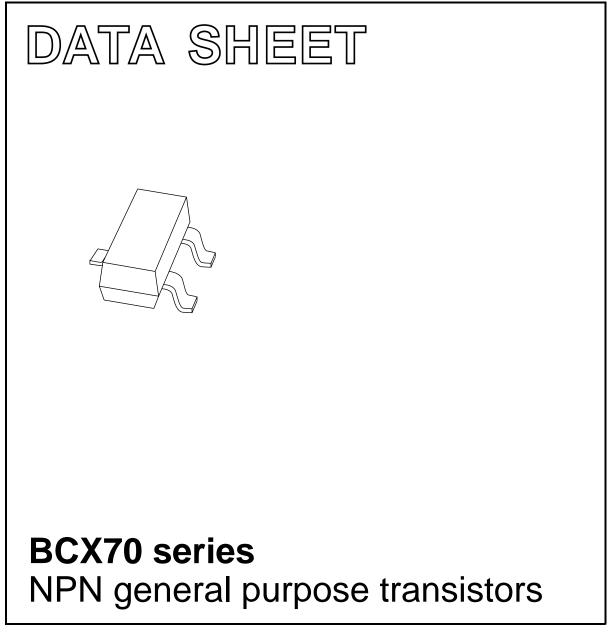
DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1999 Apr 15 2004 Jan 16



FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

APPLICATIONS

• General purpose switching and amplification.

DESCRIPTION

NPN transistor in a SOT23 plastic package. PNP complements: BCX71 series.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
BCX70G	AG*
BCX70H	AH*
BCX70J	AJ*
BCX70K	AK*

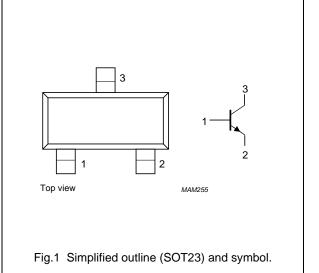
Note

- 1. * = p: Made in Hong Kong.
 - * = t : Made in Malaysia.
 - * = W : Made in China.

ORDERING INFORMATION

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



TYPE		PACKAGE		
NUMBER NAME		DESCRIPTION	VERSION	
BCX70G	_	plastic surface mounted package; 3 leads	SOT23	
BCX70H				
BCX70J				
BCX70K				

BCX70 series

BCX70 series

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	-	45	V
V _{CEO}	collector-emitter voltage	open base	-	45	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current (DC)		-	100	mA
I _{CM}	peak collector current		-	200	mA
I _{BM}	peak base current		-	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	-	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W	

Note

1. Transistor mounted on an FR4 printed-circuit board.

BCX70 series

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

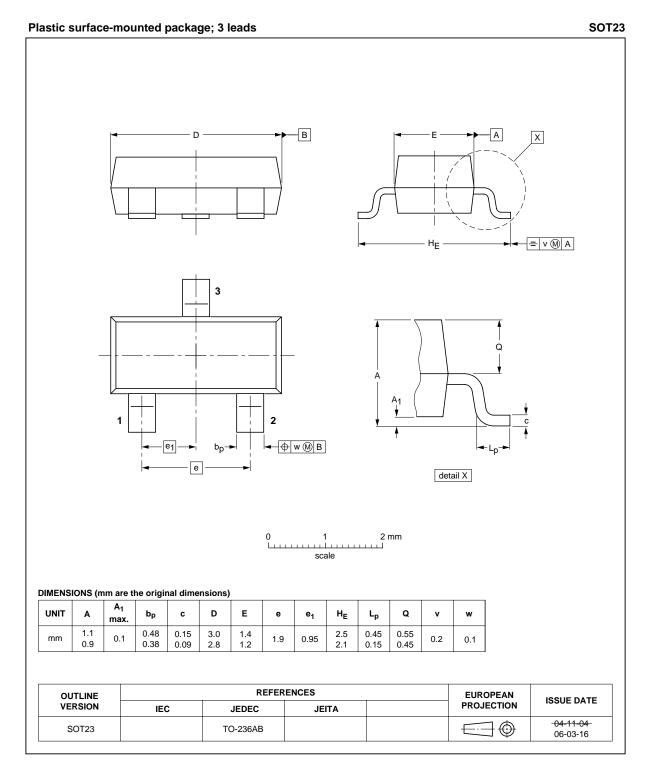
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 45 V	-	_	20	nA
		$I_E = 0; V_{CB} = 45 \text{ V}; T_{amb} = 150 ^{\circ}\text{C}$	-	-	20	μΑ
I _{EBO}	emitter cut-off current	$I_{C} = 0; V_{EB} = 4 V$	-	-	20	nA
h _{FE}	DC current gain	$I_{C} = 10 \ \mu A; V_{CE} = 5 \ V$				
	BCX70G		_	_	-	
	BCX70H		40	_	-	
	BCX70J		30	_	-	
	BCX70K		100	_	-	
	DC current gain	I _C = 2 mA; V _{CE} = 5 V				
	BCX70G		120	_	220	
	BCX70H		180	_	310	
	BCX70J		250	_	460	
	BCX70K		380	_	630	
	DC current gain	I _C = 50 mA; V _{CE} = 1 V				
	BCX70G		50	_	-	
	BCX70H		70	_	-	
	BCX70J		90	_	-	
	BCX70K		100	_	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 0.25 mA	50	-	350	mV
		I _C = 50 mA; I _B = 1.25 mA	100	-	550	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 10 mA; I _B = 0.25 mA	600	-	850	mV
		I _C = 50 mA; I _B = 1.25 mA	700	-	1050	mV
V _{BE}	base-emitter voltage	$I_{C} = 10 \ \mu A; V_{CE} = 5 \ V$	-	520	-	mV
		I _C = 2 mA; V _{CE} = 5 V	550	650	750	mV
		I _C = 50 mA; V _{CE} = 1 V	-	780	-	mV
Cc	collector capacitance	I _E = i _e = 0; V _{CB} = 10 V; f = 1 MHz	_	1.7	-	pF
C _e	emitter capacitance	$I_{C} = i_{c} = 0; V_{EB} = 0.5 V; f = 1 MHz$	-	11	-	pF
f _T	transition frequency	I_{C} = 10 mA; V_{CE} = 5 V; f = 100 MHz; note 1	100	250	-	MHz
F	noise figure	I_{C} = 200 μA; V _{CE} = 5 V; R _S = 2 kΩ; f = 1 kHz; B = 200 Hz	-	2	6	dB

Note

1. Pulse test: $t_p \leq 300~\mu\text{s};~\delta \leq 0.02.$

BCX70 series

PACKAGE OUTLINE



2004 Jan 16

BCX70 series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION	
Objective data sheet	Development	This document contains data from the objective specification for product development.	
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.	
Product data sheet	Production	This document contains the product specification.	

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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